



# **ISC Silicon NPN Power Transistor**

## **DESCRIPTION**

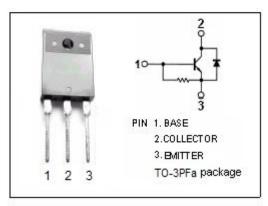
- · Collector-Base Breakdown Voltage-
  - : V<sub>CBO</sub>= 1300V (Min.)
- · High Switching Speed
- · Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

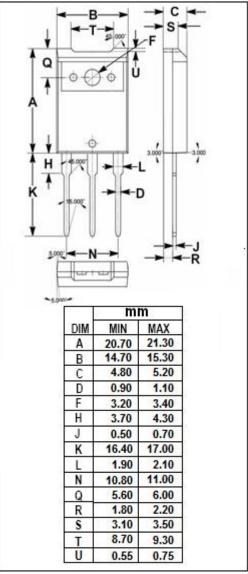
#### **APPLICATIONS**

· Designed for horizontal deflection output applications

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

ABSOLUTE MAXIMUM KATINGS(Ta=25 C)								
SYMBOL	PARAMETER	VALUE	UNIT					
Vсво	Collector- Base Voltage	1300	V					
V <sub>CES</sub>	Collector-Emitter Voltage	1300	V					
V <sub>EBO</sub>	Emitter-Base Voltage	7	V					
Ic	Collector Current-Continuous	2.5	А					
I <sub>CM</sub>	Collector Current-Peak	7	Α					
l <sub>Β</sub>	Base Current- Continuous	1.5	Α					
P <sub>C</sub>	Collector Power Dissipation @ T <sub>a</sub> =25°C	3						
	Collector Power Dissipation @ T <sub>c</sub> =25℃	60	W					
TJ	Junction Temperature 150		$^{\circ}$ C					
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$					







#### isc Silicon NPN Power Transistor

2SD1845

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

16-25 C uniess otherwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 200mA; I <sub>C</sub> = 0	7			V			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	Ic= 2A; I <sub>B</sub> = 0.6A			8.0	V			
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.6A			1.5	V			
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 750V; I <sub>E</sub> = 0 V <sub>CB</sub> = 1300V; I <sub>E</sub> = 0			10 1.0	μA mA			
h <sub>FE-1</sub>	DC Current Gain	Ic= 0.5A; VcE= 5V	5		25				
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 10V	3.5						
f⊤	Current-Gain—Bandwidth Product	Ic= 0.5A; VcE= 10V		2		MHz			
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>F</sub> = 2.5A			2.0	V			
Switching times, Resistive Load									
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 2A; I <sub>B1</sub> = 0.6A; I <sub>B2</sub> = 1.2A;		1.5		μ <b>S</b>			
t <sub>f</sub>	Fall Time	V <sub>CC</sub> = 200V		0.2		μ <b>S</b>			

## **NOTICE:**

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